

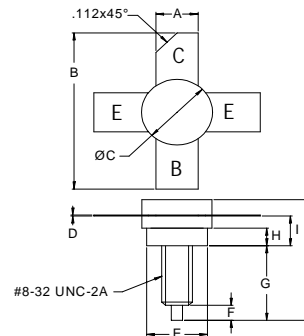
NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF238** is Designed for 13.6 V FM Large-Signal Amplifier Applications to 175 MHz.

MAXIMUM RATINGS

I_C	5.0 A (CONT)
V_{CE}	18 V
V_{CB}	60 V
P_{DISS}	65 W @ T _C = 25 °C
T_{STG}	-65 °C to +150 °C

PACKAGE STYLE .380" 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 15 mA	36			V
BV_{CEO}	I _C = 100 mA	18			V
BV_{EBO}	I _E = 5.0 mA	4.0			V
I_{CBO}	V _{CB} = 30 V			2.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	5.0			---
C_{ob}	V _{CB} = 15 V f = 1.0 MHz		105	130	pF
G_{PE} η	V _{CC} = 13.6 V P _{out} = 30 W f = 160 MHz	9.0 60	10		dB %